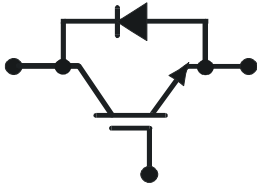


$V_{CE} = 4500\text{ V}$   
 $I_C = 1200\text{ A}$

**ABB HiPak™**

**IGBT Module**  
**5SNA 1200G450300**



Doc. No. 5SYA 1401-01 Mar 09

- Ultra low-loss, rugged SPT<sup>+</sup> chip-set
- Smooth switching SPT<sup>+</sup> chip-set for good EMC
- Industry standard package
- High power density
- AISiC base-plate for high power cycling capability
- AlN substrate for low thermal resistance



**Maximum rated values <sup>1)</sup>**

Parameter	Symbol	Conditions	min	max	Unit
Collector-emitter voltage	$V_{CES}$	$V_{GE} = 0\text{ V}$		4500	V
DC collector current	$I_C$	$T_c = 85\text{ °C}$		1200	A
Peak collector current	$I_{CM}$	$t_p = 1\text{ ms}, T_c = 85\text{ °C}$		2400	A
Gate-emitter voltage	$V_{GES}$		-20	20	V
Total power dissipation	$P_{tot}$	$T_c = 25\text{ °C}$ , per switch (IGBT)		10500	W
DC forward current	$I_F$			1200	A
Peak forward current	$I_{FRM}$			2400	A
Surge current	$I_{FSM}$	$V_R = 0\text{ V}, T_{vj} = 125\text{ °C}$ , $t_p = 10\text{ ms}$ , half-sinewave		9000	A
IGBT short circuit SOA	$t_{psc}$	$V_{CC} = 3400\text{ V}, V_{CEMCHIP} \leq 4500\text{ V}$ $V_{GE} \leq 15\text{ V}, T_{vj} \leq 125\text{ °C}$		10	$\mu\text{s}$
Isolation voltage	$V_{isol}$	1 min, $f = 50\text{ Hz}$		7400	V
Junction temperature	$T_{vj}$			125	°C
Junction operating temperature	$T_{vj(op)}$		-40	125	°C
Case temperature	$T_c$		-40	125	°C
Storage temperature	$T_{stg}$		-40	125	°C
Mounting torques <sup>2)</sup>	$M_s$	Base-heatsink, M6 screws	4	6	Nm
	$M_{t1}$	Main terminals, M8 screws	8	10	
	$M_{t2}$	Auxiliary terminals, M4 screws	2	3	

<sup>1)</sup> Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747

<sup>2)</sup> For detailed mounting instructions refer to ABB Document No. 5SYA2039

**ABB Switzerland Ltd, Semiconductors reserves the right to change specifications without notice.**



IGBT characteristic values <sup>3)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector (-emitter) breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$ , $I_C = 10 \text{ mA}$ , $T_{vj} = 25 \text{ °C}$	4500			V
Collector-emitter <sup>4)</sup> saturation voltage	$V_{CE \text{ sat}}$	$I_C = 1200 \text{ A}$ , $V_{GE} = 15 \text{ V}$		2.6		V
		$T_{vj} = 25 \text{ °C}$				V
		$T_{vj} = 125 \text{ °C}$		3.55		V
Collector cut-off current	$I_{CES}$	$V_{CE} = 4500 \text{ V}$ , $V_{GE} = 0 \text{ V}$			12	mA
		$T_{vj} = 25 \text{ °C}$			120	mA
		$T_{vj} = 125 \text{ °C}$				mA
Gate leakage current	$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$ , $T_{vj} = 125 \text{ °C}$	-500		500	nA
Gate-emitter threshold voltage	$V_{GE(TO)}$	$I_C = 240 \text{ mA}$ , $V_{CE} = V_{GE}$ , $T_{vj} = 25 \text{ °C}$	4.5		6.5	V
Gate charge	$Q_{ge}$	$I_C = 1200 \text{ A}$ , $V_{CE} = 2800 \text{ V}$ , $V_{GE} = -15 \text{ V} \dots 15 \text{ V}$		8.86		$\mu\text{C}$
Input capacitance	$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $T_{vj} = 25 \text{ °C}$		120		nF
Output capacitance	$C_{oes}$			6.02		
Reverse transfer capacitance	$C_{res}$			2.58		
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 2800 \text{ V}$ , $I_C = 1200 \text{ A}$ , $R_G = 1.5 \text{ }\Omega$ , $C_{GE} = 220 \text{ nF}$ ,	$T_{vj} = 25 \text{ °C}$	740		ns
		$V_{GE} = \pm 15 \text{ V}$ ,	$T_{vj} = 125 \text{ °C}$	750		
Rise time	$t_r$	$L_\sigma = 150 \text{ nH}$ , inductive load	$T_{vj} = 25 \text{ °C}$	210		ns
			$T_{vj} = 125 \text{ °C}$	230		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 2800 \text{ V}$ , $I_C = 1200 \text{ A}$ , $R_G = 1.5 \text{ }\Omega$ , $C_{GE} = 220 \text{ nF}$ ,	$T_{vj} = 25 \text{ °C}$	2280		ns
		$V_{GE} = \pm 15 \text{ V}$ ,	$T_{vj} = 125 \text{ °C}$	2470		
Fall time	$t_f$	$L_\sigma = 150 \text{ nH}$ , inductive load	$T_{vj} = 25 \text{ °C}$	600		ns
			$T_{vj} = 125 \text{ °C}$	660		
Turn-on switching energy	$E_{on}$	$V_{CC} = 2800 \text{ V}$ , $I_C = 1200 \text{ A}$ , $R_G = 1.5 \text{ }\Omega$ , $C_{GE} = 220 \text{ nF}$ , $V_{GE} = \pm 15 \text{ V}$ ,	$T_{vj} = 25 \text{ °C}$	3080		mJ
		$L_\sigma = 150 \text{ nH}$ , inductive load	$T_{vj} = 125 \text{ °C}$	4350		
Turn-off switching energy	$E_{off}$	$V_{CC} = 2800 \text{ V}$ , $I_C = 1200 \text{ A}$ , $R_G = 1.5 \text{ }\Omega$ , $C_{GE} = 220 \text{ nF}$ , $V_{GE} = \pm 15 \text{ V}$ ,	$T_{vj} = 25 \text{ °C}$	4960		mJ
		$L_\sigma = 150 \text{ nH}$ , inductive load	$T_{vj} = 125 \text{ °C}$	6000		
Short circuit current	$I_{SC}$	$t_{psc} \leq 10 \text{ }\mu\text{s}$ , $V_{GE} = 15 \text{ V}$ , $T_{vj} = 125 \text{ °C}$ , $V_{CC} = 3400 \text{ V}$ , $V_{CEM \text{ CHIP}} \leq 4500 \text{ V}$		5200		A
Module stray inductance	$L_{\sigma \text{ CE}}$			18		nH
Resistance, terminal-chip	$R_{CC'+EE'}$		$T_C = 25 \text{ °C}$	0.07		m $\Omega$
			$T_C = 125 \text{ °C}$	0.1		

<sup>3)</sup> Characteristic values according to IEC 60747 – 9<sup>4)</sup> Collector-emitter saturation voltage is given at chip level

**Diode characteristic values**<sup>5)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage <sup>6)</sup>	$V_F$	$I_F = 1200\text{ A}$	$T_{vj} = 25\text{ °C}$	3.2		V
			$T_{vj} = 125\text{ °C}$		3.5	
Reverse recovery current	$I_{rr}$	$V_{CC} = 2800\text{ V},$ $I_F = 1200\text{ A},$	$T_{vj} = 25\text{ °C}$	1460		A
			$T_{vj} = 125\text{ °C}$	1600		
Recovered charge	$Q_{rr}$	$V_{GE} = \pm 15\text{ V},$ $R_G = 1.5\ \Omega,$	$T_{vj} = 25\text{ °C}$	1030		$\mu\text{C}$
			$T_{vj} = 125\text{ °C}$	1660		
Reverse recovery time	$t_{rr}$	$C_{GE} = 220\text{ nF},$ $L_{\sigma} = 150\text{ nH}$ inductive load	$T_{vj} = 25\text{ °C}$	1270		ns
			$T_{vj} = 125\text{ °C}$	1860		
Reverse recovery energy	$E_{rec}$		$T_{vj} = 25\text{ °C}$	1630		mJ
			$T_{vj} = 125\text{ °C}$	2730		

<sup>5)</sup> Characteristic values according to IEC 60747 – 2<sup>6)</sup> Forward voltage is given at chip level**Package properties**<sup>7)</sup>

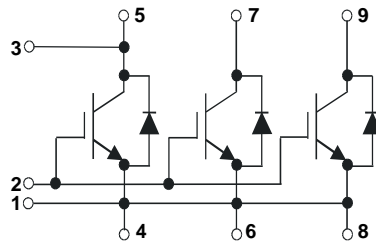
Parameter	Symbol	Conditions	min	typ	max	Unit
IGBT thermal resistance junction to case	$R_{th(j-c)IGBT}$				0.0095	K/W
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$				0.019	K/W
IGBT thermal resistance <sup>2)</sup> case to heatsink	$R_{th(c-s)IGBT}$	IGBT per switch, $\lambda$ grease = $1\text{W/m}^2\text{K}$		0.009		K/W
Diode thermal resistance <sup>7)</sup> case to heatsink	$R_{th(c-s)DIODE}$	Diode per switch, $\lambda$ grease = $1\text{W/m}^2\text{K}$		0.018		K/W
Partial discharge extinction voltage	$V_e$	$f = 50\text{ Hz}, Q_{PD} \leq 10\text{pC}$ (acc. to IEC 61287)	3500			V
Comparative tracking index	CTI			$\geq 600$		

<sup>2)</sup> For detailed mounting instructions refer to ABB Document No. 5SYA2039**Mechanical properties**<sup>7)</sup>

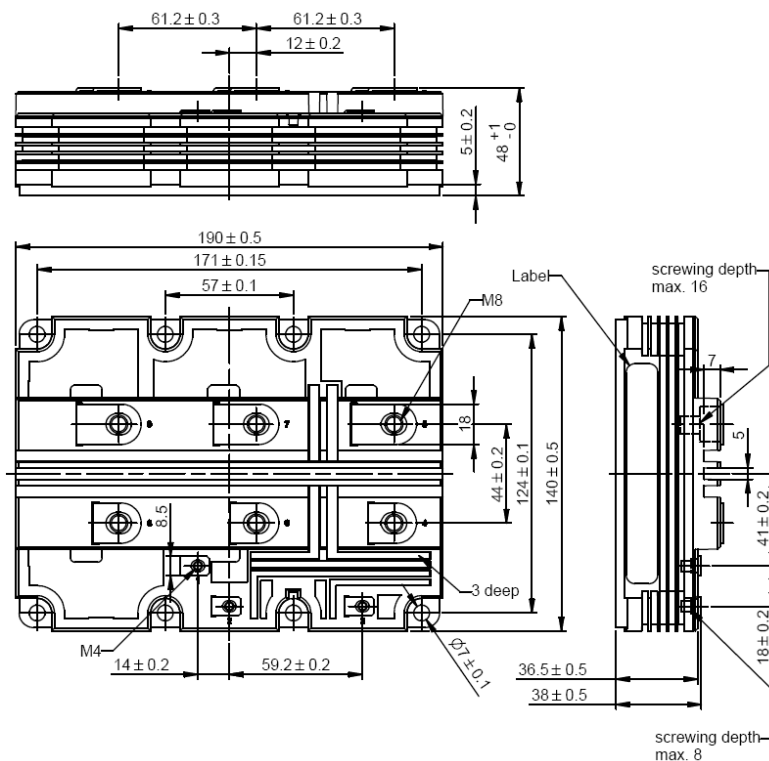
Parameter	Symbol	Conditions	min	typ	max	Unit
Dimensions	$L \times W \times H$	Typical, see outline drawing	190 × 140 × 48			mm
Clearance distance in air	$d_a$	according to IEC 60664-1 and EN 50124-1	Term. to base:	40		mm
			Term. to term:	26		
Surface creepage distance	$d_s$	according to IEC 60664-1 and EN 50124-1	Term. to base:	64		mm
			Term. to term:	56		
Mass	$m$			1760		g

<sup>7)</sup> Package and mechanical properties according to IEC 60747 – 15

## Electrical configuration



## Outline drawing <sup>2)</sup>

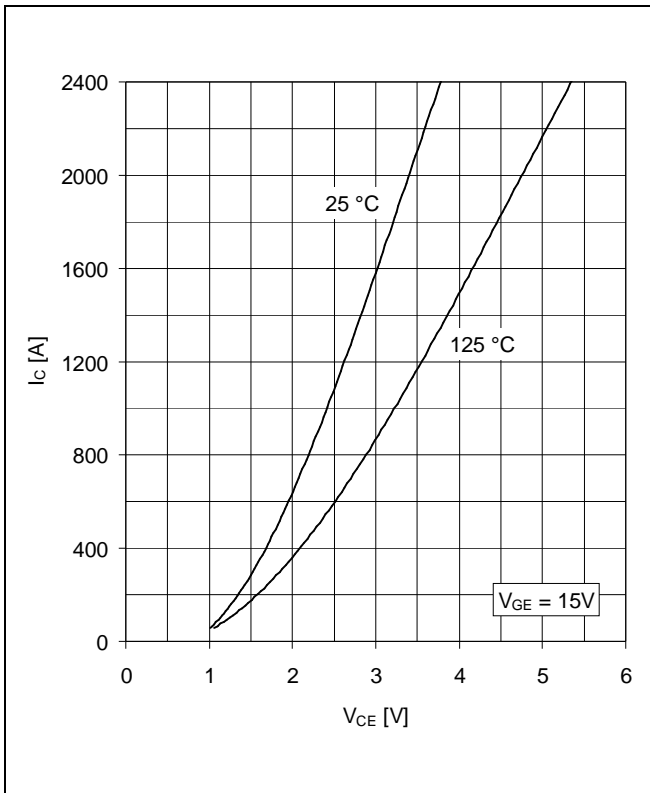


**Note: all dimensions are shown in mm**

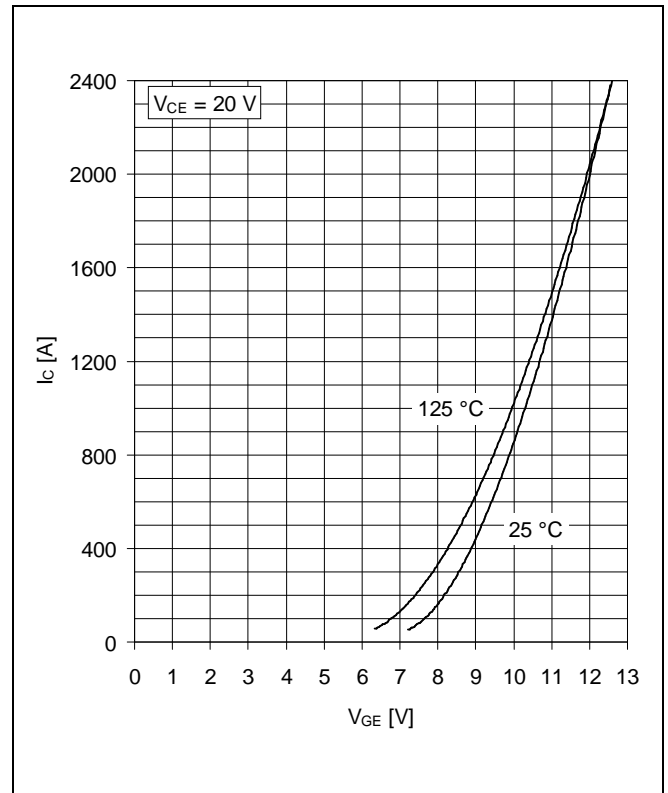
<sup>2)</sup> For detailed mounting instructions refer to ABB Document No. 5SYA2039

**This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chap. IX.**

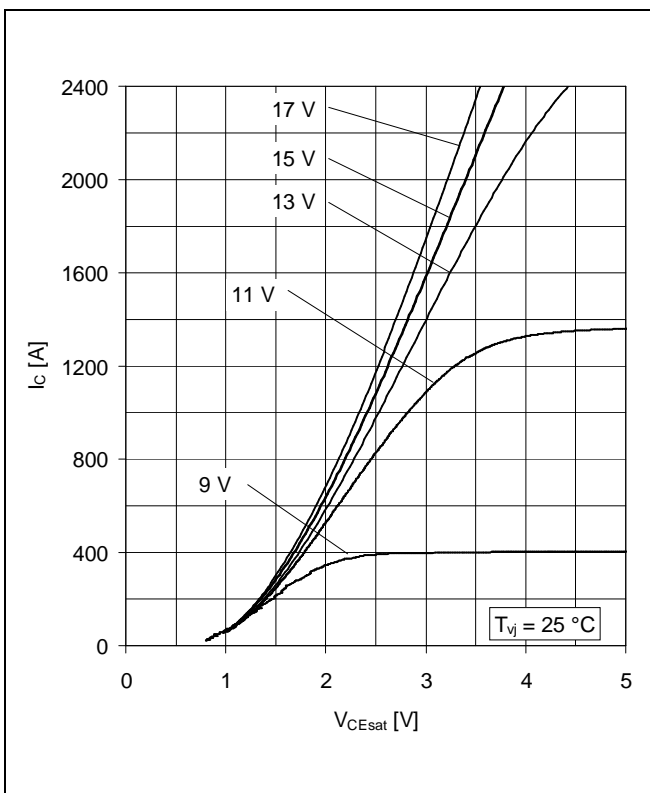
**This product has been designed and qualified for Industrial Level.**



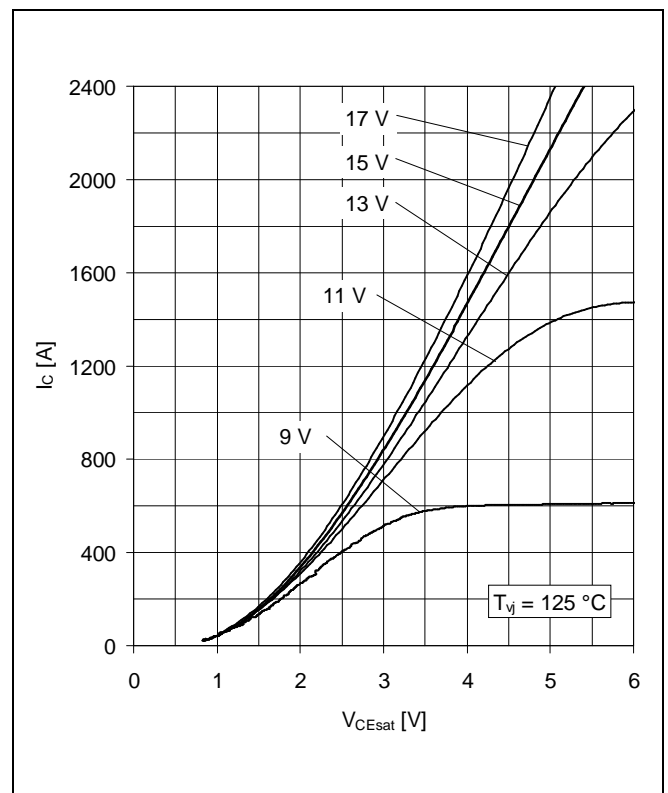
**Fig. 1** Typical on-state characteristics, chip level



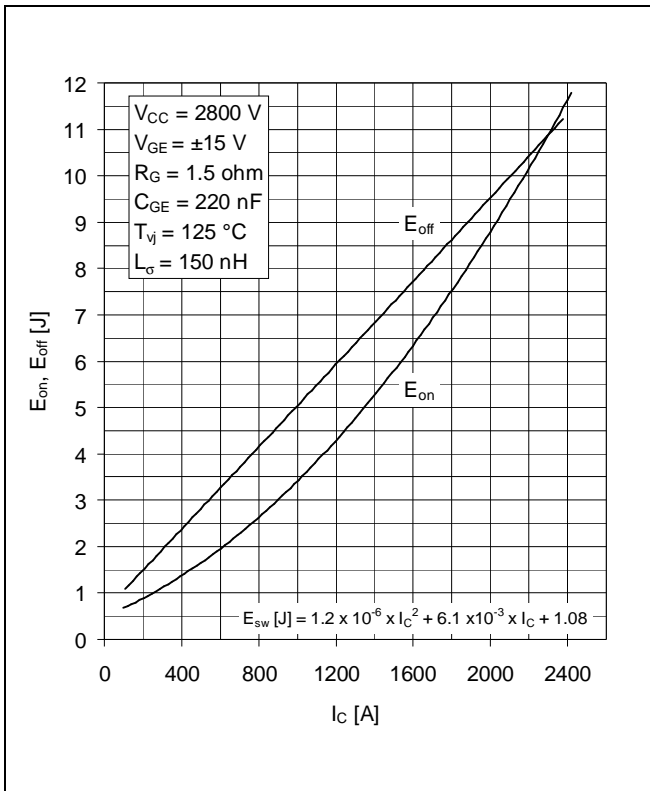
**Fig. 2** Typical transfer characteristics, chip level



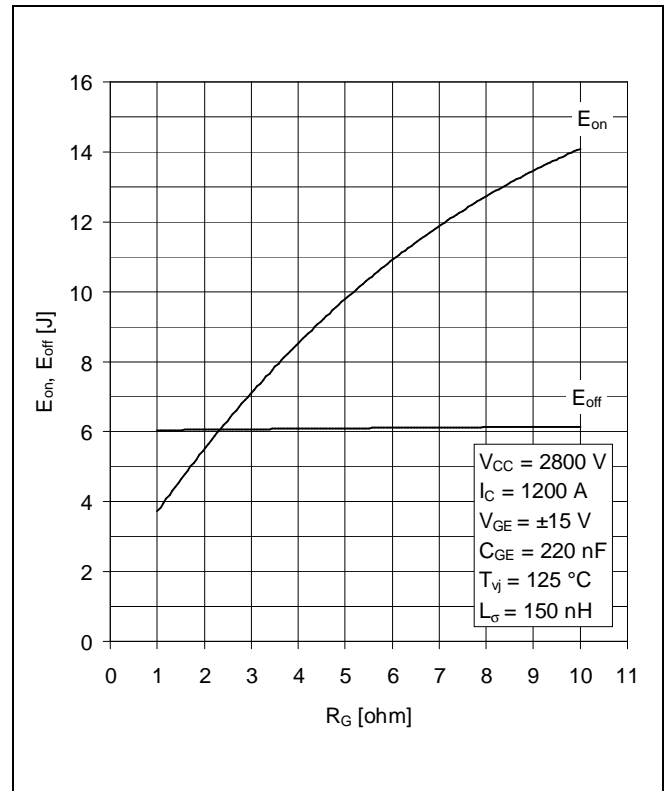
**Fig. 3** Typical output characteristics, chip level



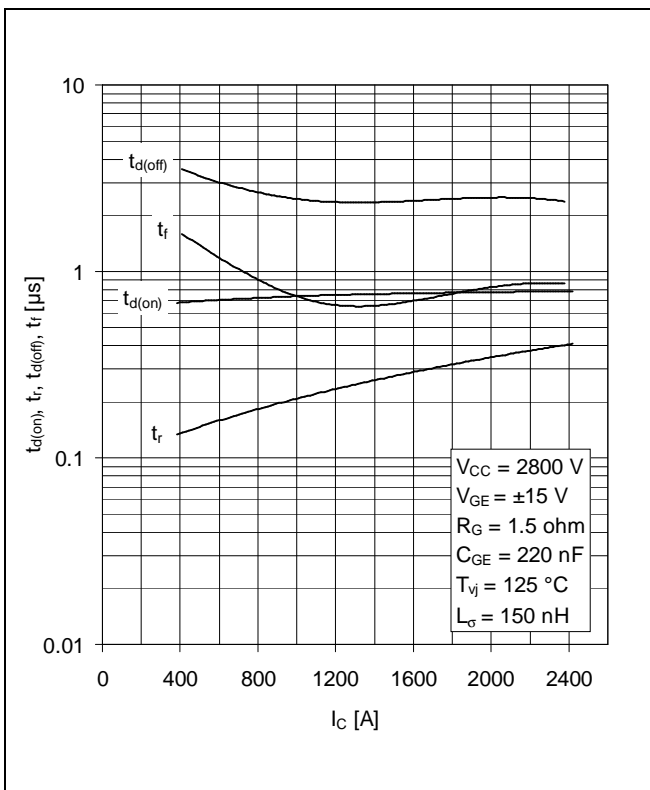
**Fig. 4** Typical output characteristics, chip level



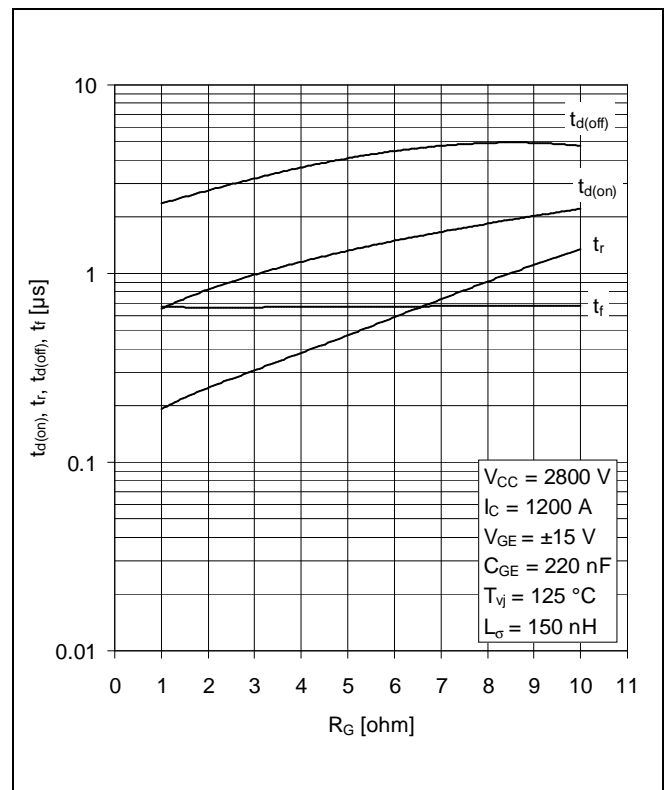
**Fig. 5** Typical switching energies per pulse vs collector current



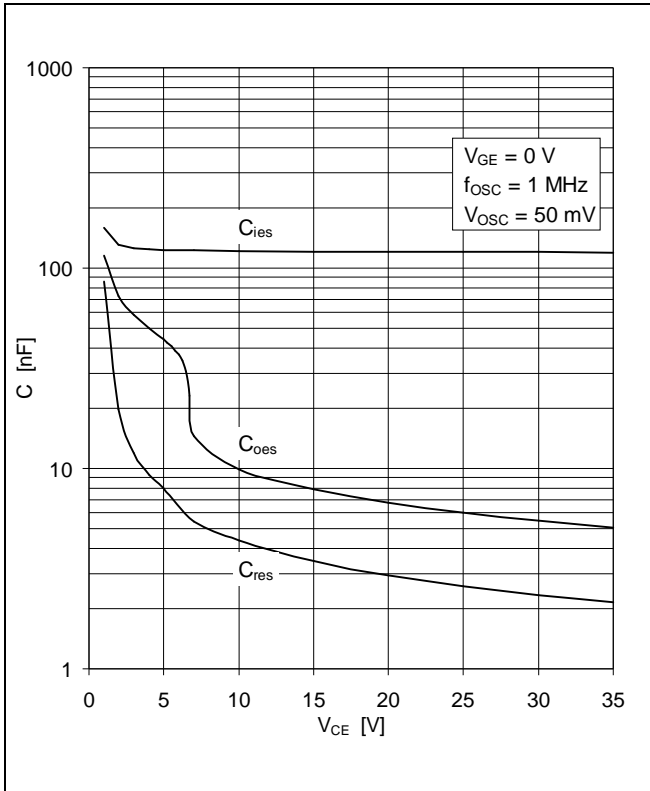
**Fig. 6** Typical switching energies per pulse vs gate resistor



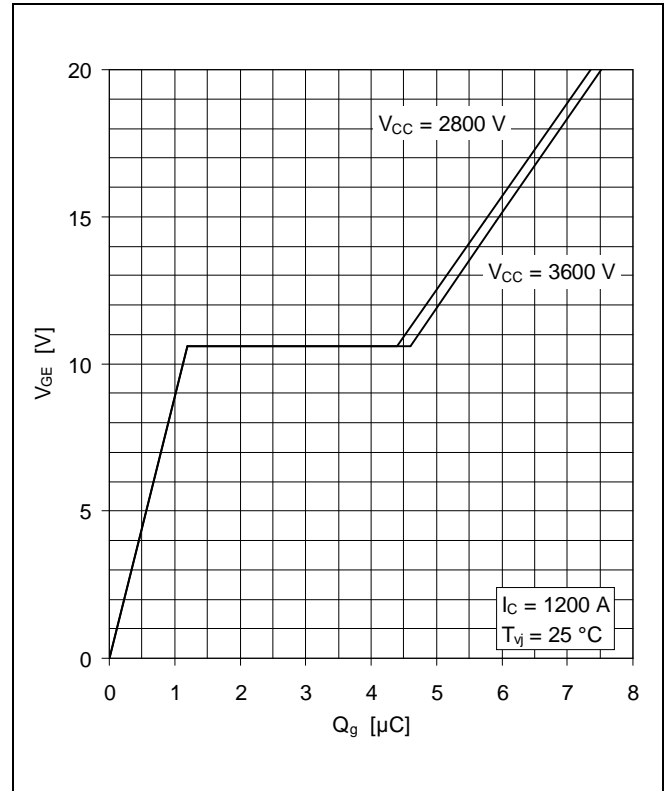
**Fig. 7** Typical switching times vs collector current



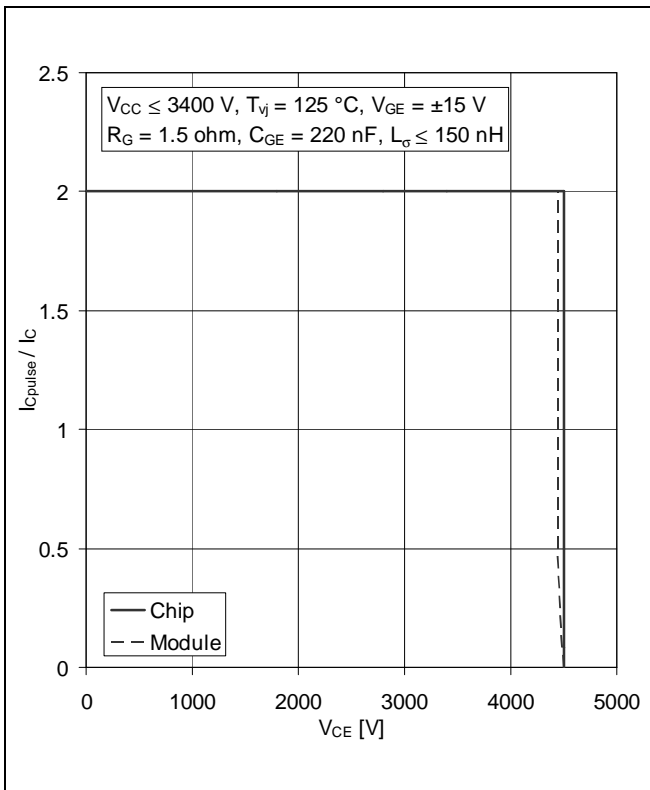
**Fig. 8** Typical switching times vs gate resistor



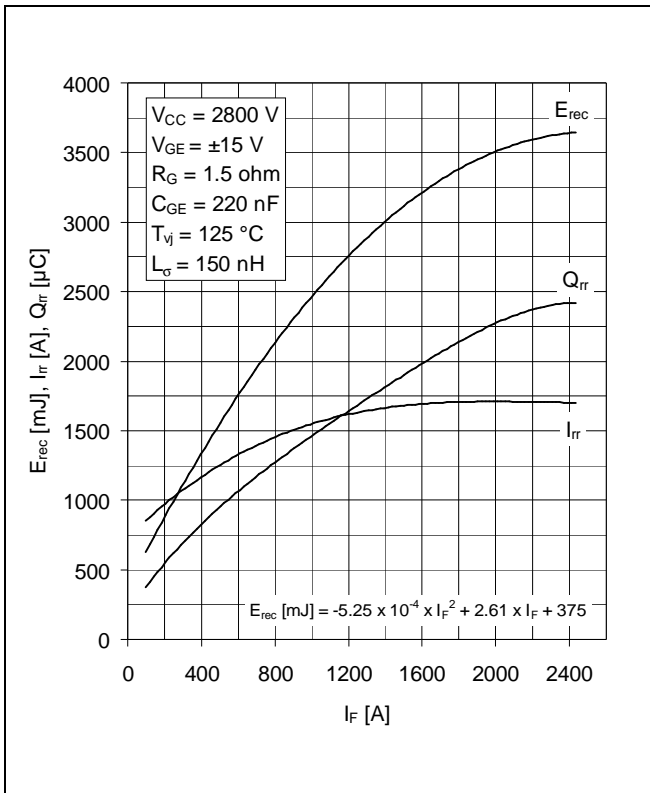
**Fig. 9** Typical capacitances vs collector-emitter voltage



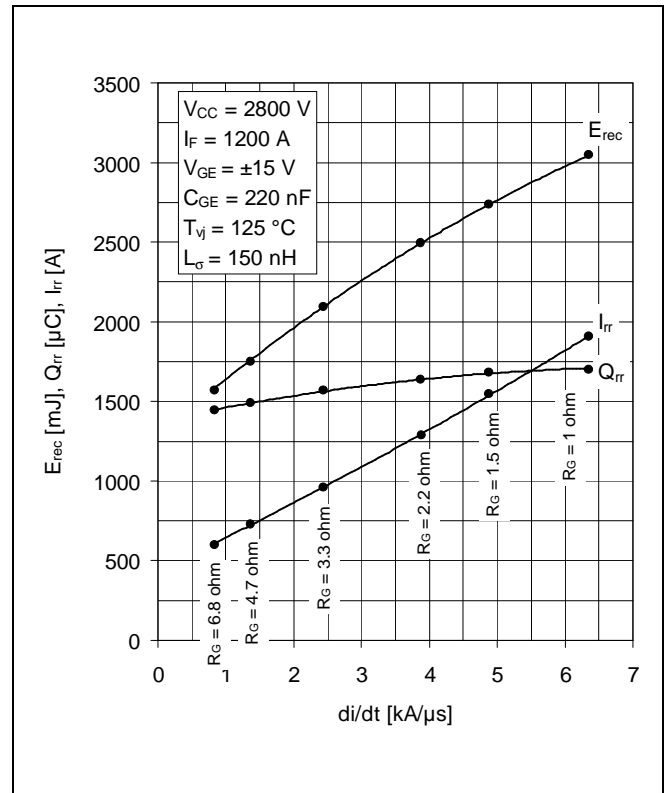
**Fig. 10** Typical gate charge characteristics



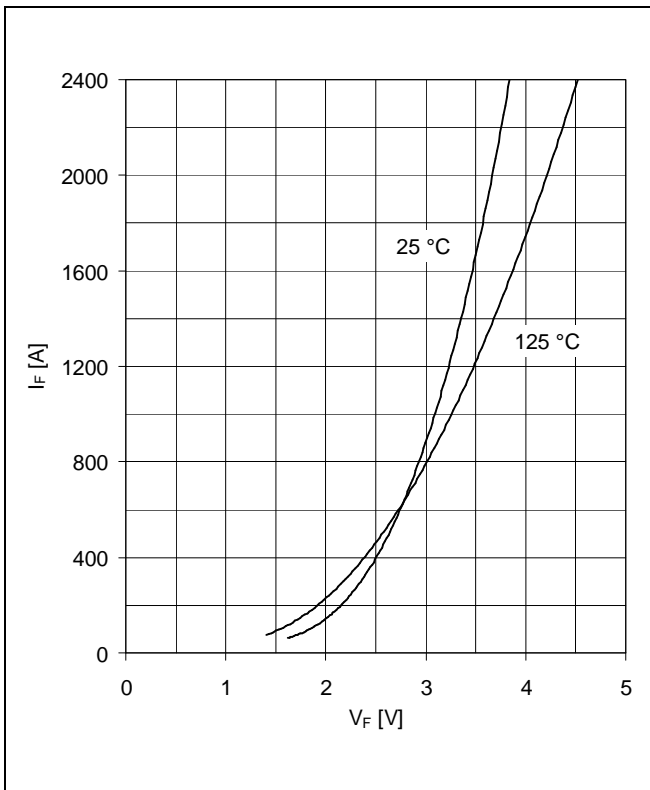
**Fig. 11** Turn-off safe operating area (RBSOA)



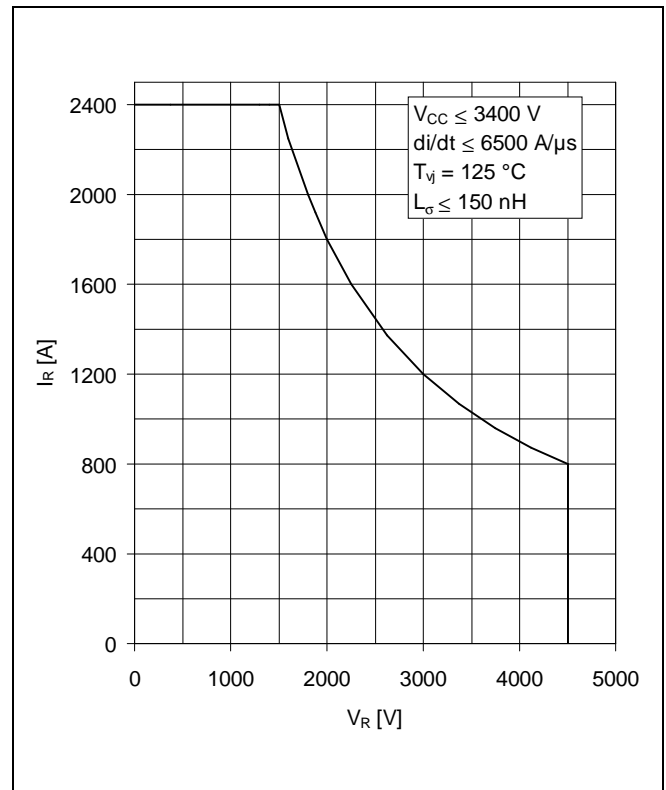
**Fig. 12** Typical reverse recovery characteristics vs forward current



**Fig. 13** Typical reverse recovery characteristics vs di/dt

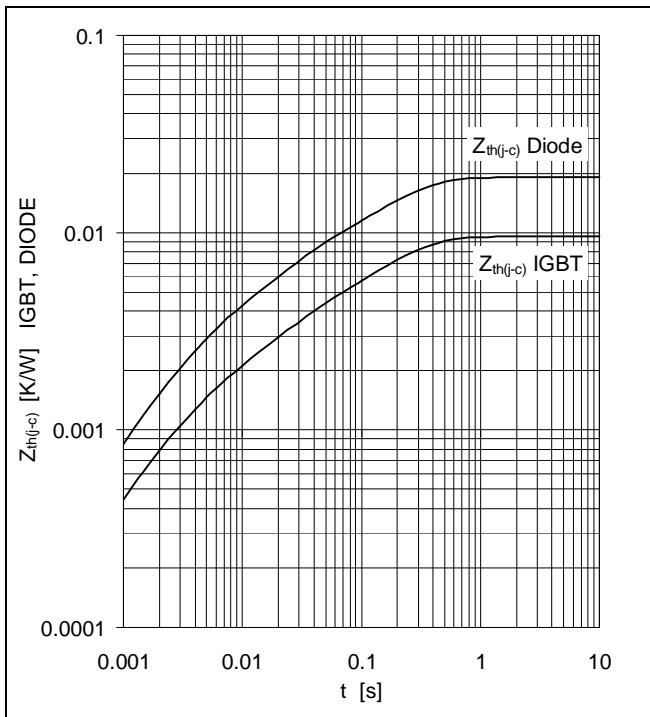


**Fig. 14** Typical diode forward characteristics, chip level



**Fig. 15** Safe operating area diode (SOA)





**Fig. 16** Thermal impedance vs time

**Analytical function for transient thermal impedance:**

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

	i	1	2	3	4	5
IGBT	R <sub>i</sub> (K/kW)	6.36	2.11	1.04		
	τ <sub>i</sub> (ms)	193	21.4	2.78		
DIODE	R <sub>i</sub> (K/kW)	12.5	4.37	2.16		
	τ <sub>i</sub> (ms)	192	22.6	3.1		

For detailed information refer to:

- 5SYA 2042 Failure rates of HiPak modules due to cosmic rays
- 5SYA 2043 Load – cycle capability of HiPaks
- 5SYA 2045 Thermal runaway during blocking
- 5SYA 2053 Applying IGBT
- 5SZK 9120 Specification of environmental class for HiPak

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